

30 V, 4.9 A NPN low V_{CEsat} (BISS) transistor Rev. 01 — 31 March 2010

Product data sheet

1. **Product profile**

1.1 General description

NPN low V_{CEsat} Breakthrough In Small Signal (BISS) transistor in a medium power SOT223 (SC-73) Surface-Mounted Device (SMD) plastic package.

PNP complement: PBSS4032PZ.

1.2 Features and benefits

- Low collector-emitter saturation voltage V_{CEsat}
- Optimized switching time
- High collector current capability I_C and I_{CM}
- High collector current gain (h_{FE}) at high I_C
- High energy efficiency due to less heat generation
- AEC-Q101 qualified
- Smaller required Printed-Circuit Board (PCB) area than for conventional transistors

1.3 Applications

- DC-to-DC conversion
- Battery-driven devices
- Power management
- Charging circuits

1.4 Quick reference data

Table 1. **Quick reference data**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{CEO}	collector-emitter voltage	open base	-	-	30	V
I _C	collector current		-	-	4.9	А
I _{CM}	peak collector current	single pulse; $t_p \leq 1 \text{ ms}$	-	-	10	А
R _{CEsat}	collector-emitter saturation resistance	I _C = 4 A; I _B = 400 mA	<u>[1]</u> -	45	62.5	mΩ

[1] Pulse test: $t_p \le 300 \ \mu s$; $\delta \le 0.02$.

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2. Pinning information

Table 2.	Pinning		
Pin	Description	Simplified outline	Graphic symbol
1	base		
2	collector		2, 4
3	emitter		1
4	collector		3
			sym016

3. Ordering information

Table 3. Ordering information						
Type number	Package	e				
	Name	Description	Version			
PBSS4032NZ	SC-73	plastic surface-mounted package with increased heat sink; 4 leads	SOT223			

4. Marking

Table 4. Marking codes	
Type number	Marking code
PBSS4032NZ	PB4032NZ

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

		•••			
Symbol	Parameter	Conditions	Min	Max	Unit
V _{CBO}	collector-base voltage	open emitter	-	30	V
V _{CEO}	collector-emitter voltage	open base	-	30	V
V _{EBO}	emitter-base voltage	open collector	-	5	V
I _C	collector current		-	4.9	А
I _{CM}	peak collector current	single pulse; $t_p \leq 1 \text{ ms}$	-	10	A
I _B	base current		-	1	А

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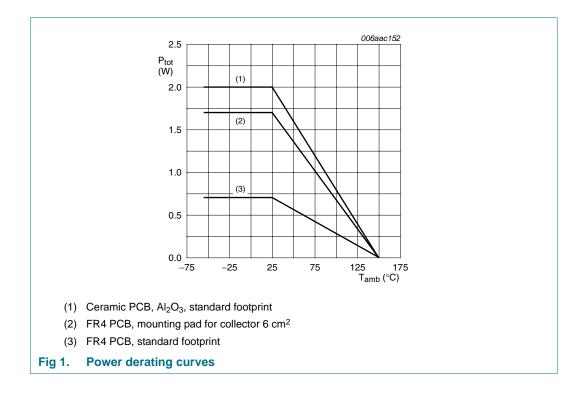
In accordance with the Absolute Maximum Rating System (IEC 60134).					
Symbol	Parameter	Conditions	Min	Max	Unit
P _{tot} total power dissipation	$T_{amb} \leq 25 ~^{\circ}C$	<u>[1]</u> _	700	mW	
			[2] _	1700	mW
			[3] _	2000	mW
Tj	junction temperature		-	150	°C
T _{amb}	ambient temperature		-55	+150	°C
T _{stg}	storage temperature		-65	+150	°C

 Table 5.
 Limiting values ...continued

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².

[3] Device mounted on a ceramic PCB, AI_2O_3 , standard footprint.



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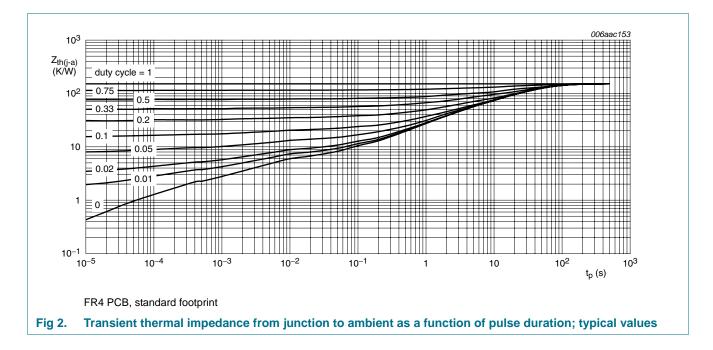
6. Thermal characteristics

Table 6.	Thermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance from	in free air	<u>[1]</u> _	-	180	K/W
	junction to ambient		[2] _	-	75	K/W
			[3] _	-	65	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point		-	-	15	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

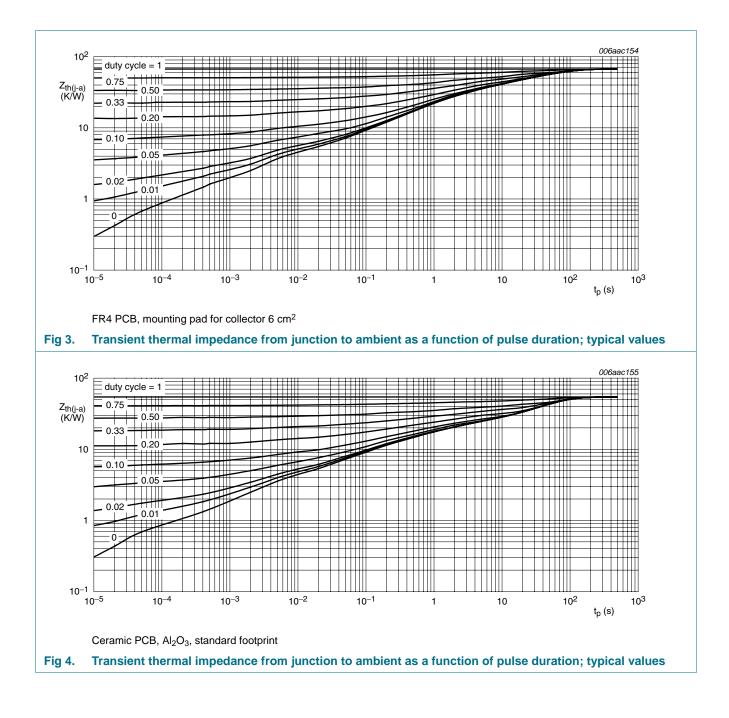
[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².

[3] Device mounted on a ceramic PCB, AI_2O_3 , standard footprint.



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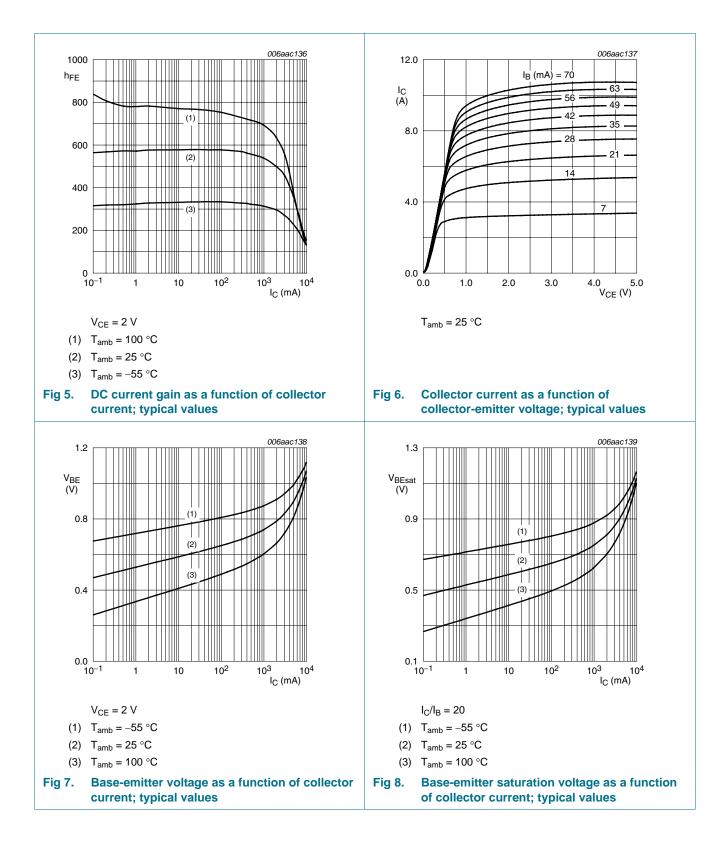
7. Characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
I _{CBO}	collector-base cut-off	V _{CB} = 30 V; I _E = 0 A		-	-	100	nA
	current	$V_{CB} = 30 \text{ V}; \text{ I}_{E} = 0 \text{ A};$ T _j = 150 °C		-	-	50	μΑ
I _{CES}	collector-emitter cut-off current	$V_{CE} = 24 \text{ V}; V_{BE} = 0 \text{ V}$		-	-	100	nA
I _{EBO}	emitter-base cut-off current	$V_{EB} = 5 \text{ V}; I_{C} = 0 \text{ A}$		-	-	100	nA
h _{FE}	DC current gain		[1]				
		$V_{CE} = 2 \text{ V}; I_{C} = 500 \text{ mA}$		300	500	-	
		$V_{CE} = 2 \text{ V}; \text{ I}_{C} = 1 \text{ A}$		300	500	-	
		$V_{CE} = 2 \text{ V}; I_{C} = 2 \text{ A}$		250	450	-	
		$V_{CE} = 2 \text{ V}; \text{ I}_{C} = 4 \text{ A}$		200	350	-	
		$V_{CE} = 2 \text{ V}; I_{C} = 6 \text{ A}$		150	275	-	
V _{CEsat}	collector-emitter		[1]				
	saturation voltage	I _C = 1 A; I _B = 50 mA		-	90	125	mV
		I _C = 1 A; I _B = 10 mA		-	130	180	mV
		$I_{C} = 2 \text{ A}; I_{B} = 40 \text{ mA}$		-	150	210	mV
		$I_{C} = 4 \text{ A}; I_{B} = 400 \text{ mA}$		-	180	250	mV
		$I_{C} = 4 \text{ A}; I_{B} = 40 \text{ mA}$		-	250	375	mV
		I _C = 5.4 A; I _B = 270 mA		-	240	340	mV
R _{CEsat}	collector-emitter saturation resistance	$I_{C} = 4 \text{ A}; I_{B} = 400 \text{ mA}$	<u>[1]</u>	-	45	62.5	mΩ
V _{BEsat}	base-emitter	$I_{C} = 1 \text{ A}; I_{B} = 100 \text{ mA}$	[1]	-	0.75	0.9	V
	saturation voltage	I _C = 4 A; I _B = 400 mA	[1]	-	0.92	1.05	V
V _{BEon}	base-emitter turn-on voltage	$V_{CE} = 2 \text{ V}; I_{C} = 2 \text{ A}$	<u>[1]</u>	-	0.77	0.85	V
t _d	delay time	$V_{CC} = 12.5 \text{ V}; I_C = 1 \text{ A};$		-	35	-	ns
t _r	rise time	I _{Bon} = 0.05 A; I _{Boff} = -0.05 A		-	30	-	ns
t _{on}	turn-on time	B ^{0#} = -0.00 X		-	65	-	ns
t _s	storage time			-	150	-	ns
t _f	fall time			-	65	-	ns
t _{off}	turn-off time			-	215	-	ns
f _T	transition frequency	V _{CE} = 10 V; I _C = 100 mA; f = 100 MHz		-	145	-	MHz
C _c	collector capacitance	$V_{CB} = 10 \text{ V}; I_E = i_e = 0 \text{ A};$ f = 1 MHz		-	65	-	pF

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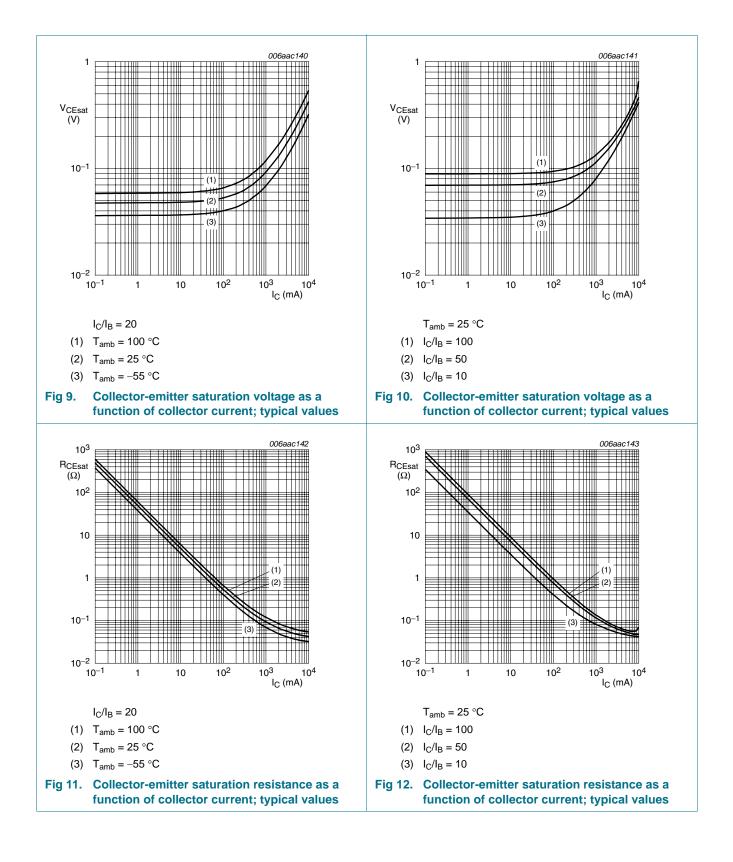
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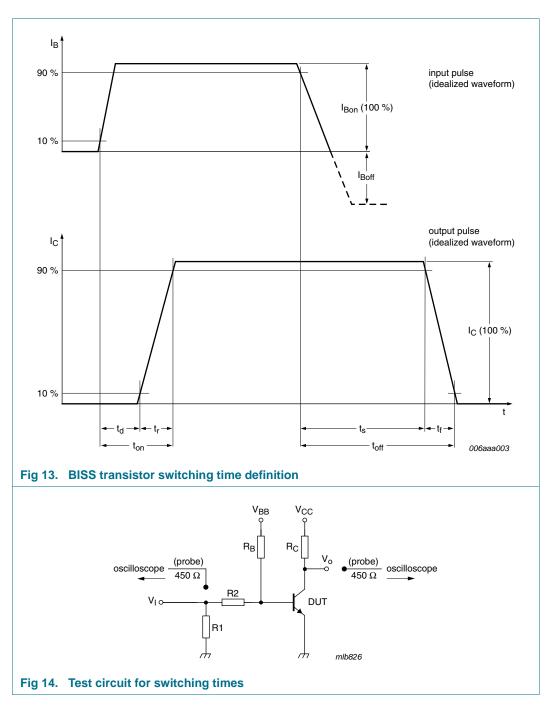
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8. Test information



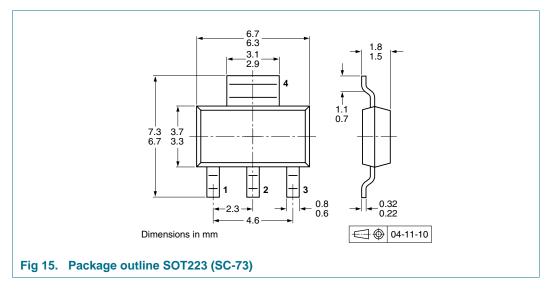
8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101* - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

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9. Package outline



10. Packing information

Table 8. Packing methods

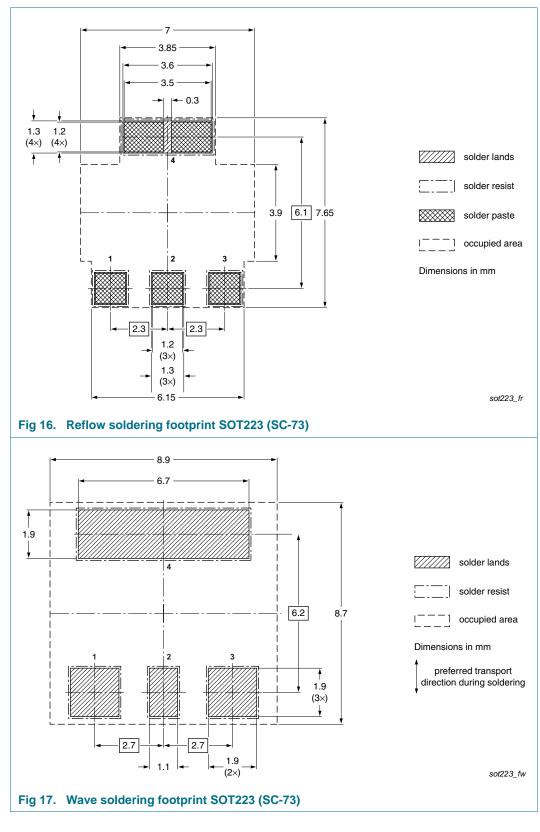
The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number	Package	Description	Packing	quantity
			1000	4000
PBSS4032NZ	SOT223	8 mm pitch, 12 mm tape and reel	-115	-135

[1] For further information and the availability of packing methods, see <u>Section 14</u>.

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11. Soldering



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12. Revision history

Table 9. Revi	Revision history				
Document ID	Release date	Data sheet status	Change notice	Supersedes	
PBSS4032NZ_1	20100331	Product data sheet	-	-	

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13. Legal information

13.1 Data sheet status

Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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